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List of Publications by Year in descending order

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87
docs citations

87
times ranked

863
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#	ARTICLE	IF	CITATIONS
1	Highly Reliable Selection Behavior With Controlled Ag Doping of Nano-Polycrystalline ZnO Layer for 3D X-Point Framework. IEEE Electron Device Letters, 2022, 43, 21-24.	3.9	1
2	Impact of thermal expansion coefficient on the local tilt angle of extreme ultraviolet pellicle. Journal of Micro-nanopatterning, Materials, and Metrology, 2022, 21, .	0.8	1
3	Investigation of the Resistivity and Emissivity of a Pellicle Membrane for EUV Lithography. Membranes, 2022, 12, 367.	3.0	4
4	Plasma-Enhanced Atomic-Layer Deposition of Nanometer-Thick SiN _x Films Using Trichlorodisilane for Etch-Resistant Coatings. ACS Applied Nano Materials, 2021, 4, 2558-2564.	5.0	8
5	Impact of residual stress on the deflection of extreme ultraviolet pellicles. Journal of Micro-nanopatterning, Materials, and Metrology, 2021, 20, .	0.8	1
6	A new route of synthesizing atomically thin 2D materials embedded in bulk oxides. Journal of Applied Physics, 2021, 130, 035302.	2.5	0
7	Nano-polycrystalline Ag-doped ZnO layer for steep-slope threshold switching selectors. AIP Advances, 2021, 11, 115213.	1.3	0
8	Microstructures of HfOx Films Prepared via Atomic Layer Deposition Using La(NO ₃) ₃ ·6H ₂ O Oxidants. Materials, 2021, 14, 7478.	2.9	5
9	A Comprehensive Study on the Effect of TiN Top and Bottom Electrodes on Atomic Layer Deposited Ferroelectric Hf _{0.5} Zr _{0.5} O ₂ Thin Films. Materials, 2020, 13, 2968.	2.9	30
10	Low Temperature Thermal Atomic Layer Deposition of Aluminum Nitride Using Hydrazine as the Nitrogen Source. Materials, 2020, 13, 3387.	2.9	12
11	High growth rate and high wet etch resistance silicon nitride grown by low temperature plasma enhanced atomic layer deposition with a novel silylamine precursor. Journal of Materials Chemistry C, 2020, 8, 13033-13039.	5.5	8
12	Enhanced resistive switching characteristics of HfOx insulator fabricated by atomic layer deposition and La(NO ₃) ₃ ·6H ₂ O solution as catalytic oxidant. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, 032405.	2.1	1
13	Fabrication of free-standing nanoscale SiN membranes with enhanced burst pressure via improved etching process. Sensors and Actuators A: Physical, 2019, 297, 111538.	4.1	3
14	Understanding of relationship between dopant and substitutional site to develop novel phase-change materials based on In ₃ SbTe ₂ . Japanese Journal of Applied Physics, 2019, 58, SBBB02.	1.5	15
15	Performance of Extreme Ultraviolet Coherent Scattering Microscope. Journal of Nanoscience and Nanotechnology, 2019, 19, 6463-6467.	0.9	4
16	Synthesis of Ag-ZnO core-shell nanoparticles with enhanced photocatalytic activity through atomic layer deposition. Materials and Design, 2019, 177, 107831.	7.0	42
17	Fe ₃ O ₄ "ZnO Core" Shell Nanoparticles Fabricated by Ultra-Thin Atomic Layer Deposition Technique as a Drug Delivery Vehicle. Electronic Materials Letters, 2019, 15, 493-499.	2.2	4
18	Crystallized ZnO films by inserting the inert metal on ITO and their improved on/off current performance. Materials Science in Semiconductor Processing, 2019, 97, 85-90.	4.0	2

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19	Interface-Driven Phase Transition of Phase-Change Material. <i>Crystal Growth and Design</i> , 2019, 19, 2123-2130.	3.0	5
20	Investigation of the Mechanical/Thermal Properties of Nano-Scale Silicon Nitride Membranes. <i>Journal of Korean Institute of Metals and Materials</i> , 2019, 57, 124-129.	1.0	5
21	Through-pellicle imaging of extreme ultraviolet mask with extreme ultraviolet ptychography microscope. <i>Journal of Micro/ Nanolithography, MEMS, and MOEMS</i> , 2019, 18, 1.	0.9	3
22	Mask Materials and Designs for Extreme Ultra Violet Lithography. <i>Electronic Materials Letters</i> , 2018, 14, 533-547.	2.2	16
23	Direct printing of soluble acene crystal stripes by a programmed dip-coating process for organic field-effect transistor applications. <i>Journal of Materials Chemistry C</i> , 2018, 6, 799-807.	5.5	21
24	Improved resistive switching characteristics of a Pt/HfO ₂ /Pt resistor by controlling anode interface with forming and switching polarity. <i>Applied Surface Science</i> , 2018, 435, 117-121.	6.1	19
25	Effects of hydrogen annealing temperature on the resistive switching characteristics of HfO _x thin films. <i>Materials Science in Semiconductor Processing</i> , 2018, 88, 207-213.	4.0	10
26	Effects of Y Dopant on Lattice Distortion and Electrical Properties of In ₃ SbTe ₂ Phase-Change Material. <i>Physica Status Solidi - Rapid Research Letters</i> , 2017, 11, 1700275.	2.4	6
27	Effects of Y Dopant on Lattice Distortion and Electrical Properties of In ₃ SbTe ₂ Phase-Change Material (Phys. Status Solidi RRL 11/2017). <i>Physica Status Solidi - Rapid Research Letters</i> , 2017, 11, 1770356.	2.4	0
28	Effects of an in vacancy on local distortion of fast phase transition in Bi-doped In ₃ SbTe ₂ . <i>Journal of the Korean Physical Society</i> , 2017, 71, 946-949.	0.7	1
29	GeO _x interfacial layer scavenging remotely induced by metal electrode in metal/HfO ₂ /GeO _x /Ge capacitors. <i>Applied Physics Letters</i> , 2016, 109, .	3.3	3
30	Fabrication of Fe ₃ O ₄ -ZnO core-shell nanoparticles by rotational atomic layer deposition and their multi-functional properties. <i>Current Applied Physics</i> , 2016, 16, 1564-1570.	2.4	10
31	Coherent scattering microscopy as an effective inspection tool for analyzing performance of phase shift mask. <i>Optics Express</i> , 2016, 24, 12055.	3.4	6
32	Phase Shift Mask to Compensate for Mask 3D Effect in High-Numerical-Aperture Extreme Ultraviolet Lithography. <i>Nanoscience and Nanotechnology Letters</i> , 2016, 8, 729-733.	0.4	1
33	Influence of Annealing Temperature on Structural and Optical Properties of Undoped and Al-Doped Nano-ZnO Films Prepared by Sol-Gel Method. <i>Science of Advanced Materials</i> , 2016, 8, 878-883.	0.7	6
34	Lattice Distortion in In ₃ SbTe ₂ Phase Change Material with Substitutional Bi. <i>Scientific Reports</i> , 2015, 5, 12867.	3.3	17
35	Resistive Switching Characteristics of Atomic-Layer-Deposited Y ₂ O ₃ Insulators with Deposition Temperature. <i>Journal of Nanoscience and Nanotechnology</i> , 2015, 15, 7586-7589.	0.9	5
36	Metal-HfO ₂ -Ge capacitor: Its enhanced charge trapping properties with S-treated substrate and atomic-layer-deposited HfO ₂ layer. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015, 33, .	2.1	4

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37	Attenuated phase-shift mask for mitigation of photon shot noise effect in contact hole pattern for extreme ultraviolet lithography. Applied Physics Express, 2014, 7, 096502.	2.4	2
38	Anode dependence of set voltage in resistive switching of metal/HfO ₂ /metal resistors. Applied Physics Letters, 2014, 105, 223512.	3.3	8
39	Actinic critical dimension measurement of contaminated extreme ultraviolet mask using coherent scattering microscopy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 031601.	1.2	3
40	Dielectric function of Si ^x Ge _x films grown on silicon-on-insulator substrates. Journal of Applied Physics, 2014, 115, 233707.	2.5	2
41	Highly sensitive wide bandwidth photodetectors using chemical vapor deposited graphene. Applied Physics Letters, 2014, 104, .	3.3	20
42	Atomic layer deposition of Y ₂ O ₃ films using heteroleptic liquid (iPrCp) ₂ Y(iPr- <i>amd</i>) precursor. Journal of Materials Chemistry C, 2014, 2, 9240-9247.	5.5	43
43	Various nanofabrication approaches towards two-dimensional photonic crystals for ceramic plate phosphor-capped white light-emitting diodes. Journal of Materials Chemistry C, 2014, 2, 7513.	5.5	26
44	Enhanced light extraction from Y ₂ O ₃ : Eu ³⁺ phosphor films via vacuum nano-imprint lithography using spin-on dielectric materials. Thin Solid Films, 2013, 547, 222-224.	1.8	3
45	Dielectric Stacking Effect of Al_2O_3 and HfO_2 in Metal-Insulator-Metal Capacitor. IEEE Electron Device Letters, 2013, 34, 120-122.	3.9	41
46	Improved imaging properties of thin attenuated phase shift masks for extreme ultraviolet lithography. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 021606.	1.2	8
47	Very Thin Extreme Ultraviolet Mask Absorber Material for Extremely Fine Pitch Patterning. Applied Physics Express, 2013, 6, 076502.	2.4	7
48	Stochastic resist patterning simulation using attenuated PSM for EUV lithography. Proceedings of SPIE, 2013, , .	0.8	2
49	Raman spectroscopic image analysis on micropatterned graphene. Micro and Nano Letters, 2013, 8, 362-365.	1.3	3
50	Effect on Critical Dimension Performance for Carbon Contamination of Extreme Ultraviolet Mask Using Coherent Scattering Microscopy and In-situ Contamination System. Japanese Journal of Applied Physics, 2012, 51, 06FB04.	1.5	1
51	Evaluation of lithographic performance of extreme ultra violet mask using coherent scattering microscope. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, .	1.2	5
52	Effect on Critical Dimension Performance for Carbon Contamination of Extreme Ultraviolet Mask Using Coherent Scattering Microscopy and In-situ Contamination System. Japanese Journal of Applied Physics, 2012, 51, 06FB04.	1.5	3
53	Nanosize Patterning with Nanoimprint Lithography Using Poly(vinyl alcohol) Transfer Layer. Japanese Journal of Applied Physics, 2011, 50, 06GG08.	1.5	0
54	Fabrication of 2D photonic crystal assisted Y ₂ O ₃ :Eu ³⁺ thin-film phosphors by direct nano-imprinting. Microelectronic Engineering, 2011, 88, 2930-2933.	2.4	9

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55	Carbon contamination of EUV mask and its effect on CD performance. Current Applied Physics, 2011, 11, S107-S110.	2.4	9
56	Annealing-induced enhancement of ferromagnetism in SnO ₂ -core/Cu-shell coaxial nanowires. Metals and Materials International, 2011, 17, 641-647.	3.4	7
57	Fabrication of trench nanostructures for extreme ultraviolet lithography masks by atomic force microscope lithography. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, 011034.	1.2	2
58	Improved electrical properties of Pt/HfO ₂ /Ge using <i>in situ</i> water vapor treatment and atomic layer deposition. Applied Physics Letters, 2011, 98, .	3.3	18
59	Nanosize Patterning with Nanoimprint Lithography Using Poly(vinyl alcohol) Transfer Layer. Japanese Journal of Applied Physics, 2011, 50, 06GG08.	1.5	0
60	Influence of MEEF change on the mask shadowing effect in extreme ultraviolet lithography. Microelectronic Engineering, 2010, 87, 2134-2138.	2.4	2
61	Infinitely high selective inductively coupled plasma etching of an indium tin oxide binary mask structure for extreme ultraviolet lithography. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2010, 28, 761-765.	2.1	4
62	Reduced Metal Contamination in Atomic-Layer-Deposited HfO ₂ Films Grown on Si Using O ₃ Oxidant Generated Without N ₂ Assistance. Electrochemical and Solid-State Letters, 2010, 13, G65.	2.2	12
63	? Optical Properties of TiO ₂ Zigzag Films Prepared by Oblique Angle Deposition. Journal of the Korean Physical Society, 2010, 56, 1378-1381.	0.7	4
64	Determination of the CD Performance and Carbon Contamination of an EUV Mask by Using a Coherent Scattering Microscopy/In-situ Contamination System. Journal of the Korean Physical Society, 2010, 57, 1486-1489.	0.7	6
65	Effect of Attenuated Phase Shift Mask Structure on Extreme Ultraviolet Lithography. Japanese Journal of Applied Physics, 2009, 48, 06FA06.	1.5	3
66	Highly selective dry etching of alternating phase-shift mask (PSM) structures for extreme ultraviolet lithography (EUVL) using inductively coupled plasmas (ICP). Thin Solid Films, 2009, 517, 3938-3941.	1.8	1
67	Dry etching of extreme ultraviolet lithography mask structures in inductively coupled plasmas. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2008, 26, 857-860.	2.1	5
68	Oxidant Effect on Resistance Switching Characteristics of HfO ₂ film Grown Atomic Layer Deposition. ECS Transactions, 2007, 11, 61-66.	0.5	6
69	Growth behavior of oxide nanostructures by electrical and thermal conductivities of substrate in atomic force microscope nano-oxidation. Journal of Applied Physics, 2007, 101, 044905.	2.5	5
70	Damage Free Particle Removal from EUVL Mask Layers by High Energy Laser Shock Cleaning (LSC). , 2007, , .		1
71	Resistance Switching Characteristics for Nonvolatile Memory Operation of Binary Metal Oxides. Japanese Journal of Applied Physics, 2007, 46, 2172-2174.	1.5	57
72	Nanoscale patterning using photo-assisted polymer transfer lithography. Microelectronic Engineering, 2007, 84, 1511-1514.	2.4	1

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73	Resistance Switching Characteristics of HfO ₂ Film with Electrode for Resistance Change Random Access Memory. Journal of Nanoscience and Nanotechnology, 2007, 7, 4139-4142.	0.9	3
74	Novel hybrid mask mold for combined nanoimprint and photolithography technique. Microelectronic Engineering, 2006, 83, 889-892.	2.4	5
75	Characterization of Ru layer for capping/buffer application in EUVL mask. Microelectronic Engineering, 2006, 83, 688-691.	2.4	16
76	Novel absorber stack for minimizing shadow effect in extreme ultraviolet mask. Journal of Vacuum Science & Technology B, 2006, 24, 2820.	1.3	11
77	Electrical Properties of Atomic Layer Deposited HfO ₂ Gate Dielectric Film Using D ₂ O as Oxidant for Improved Reliability. Japanese Journal of Applied Physics, 2006, 45, 6993-6995.	1.5	3
78	Dry etching of TaN/HfO ₂ gate-stack structure in BCl ₃ /Ar/O ₂ inductively coupled plasmas. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 1373-1379.	2.1	34
79	Characterization and evaluation of ALD-HfO ₂ using H ₂ O and D ₂ O as an oxidant. , 2005, , .		0
80	Numerical investigation of defect printability in extreme ultraviolet (EUV) reflector: Ru/Mo/Si multilayer system. , 2004, , .		0
81	Enhancement of EUV Reflective Multilayer Properties by the Insertion of a Ru Barrier Layer. Journal of the Korean Physical Society, 2003, 43, 826-830.	0.7	6
82	Analysis of Multilayer Structure for Reflection of Extreme-Ultraviolet Wavelength. Japanese Journal of Applied Physics, 2002, 41, 4086-4090.	1.5	6
83	A study on the properties of interlayer low dielectric polyimide during Cl-based plasma etching of aluminum. , 0, , .		0
84	Comparison of Pt etching characteristics with SF ₆ and Cl ₂ plasma chemistries. , 0, , .		0
85	Enhancement of EUV reflective multilayer properties by the insertion of Ru barrier layer. , 0, , .		0
86	Structural characterization of Mo/Ru/Si EUV reflector by optical modeling. , 0, , .		0
87	Verification of phase defect correctability of EUV reflective multilayer. , 0, , .		0